

10W AUDIO AMPLIFIER WITH MUTING

DESCRIPTION

The TDA 1910 is a monolithic integrated circuit in MULTIWATT® package, intended for use in Hi-Fi audio power applications, as high quality TV sets.

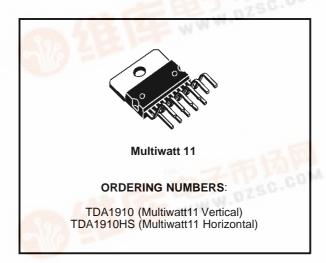
The TDA 1910 meets the DIN 45500 (d = 0.5%) guaranteed output power of 10W when used at 24V/4W. At 24V/8W the output power is 7W min. Features:

- muting facility
- protection against chip over temperature
- very low noise
- high supply voltage rejection
- low "switch-on" noise.

The TDA 1910 is assembled in MULTIWATT® package that offers:

- easy assembly
- simple heatsink

ABSOLUTE MAXIMUM RATINGS

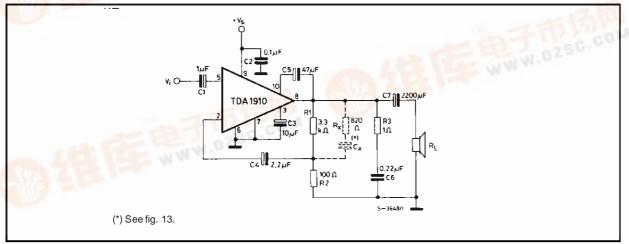


space and cost saving

- high reliability

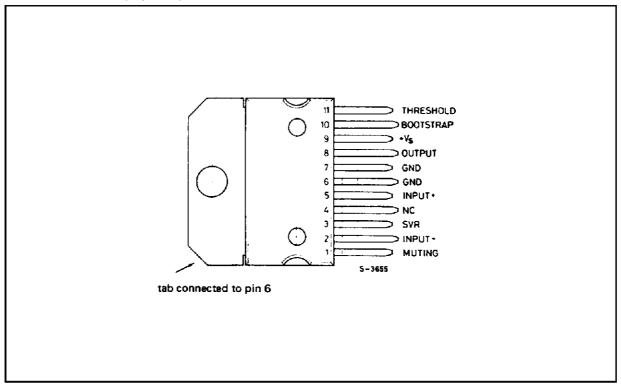
Symbol	Parameter	Value	Unit V	
Vs	Supply voltage	30		
lo	Output peak current (non repetitive)	3.5	A	
lo	Output peak current (repetitive)	3.0	A	
Vi	Input voltage	$0 \text{ to } + \text{V}_{\text{s}}$	V	
Vi	Differential input voltage	±7	V	
V ₁₁	Muting thresold voltage	Vs	V	
Ptot	Power dissipation at T _{case} = 90°C	20	W	
T _{stq} , T _j	Storage and junction temperature	-40 to 150	°C	

TEST CIRCUIT

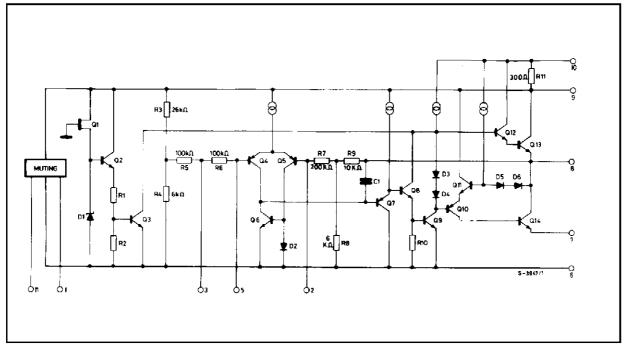




PIN CONNECTION (Top view)

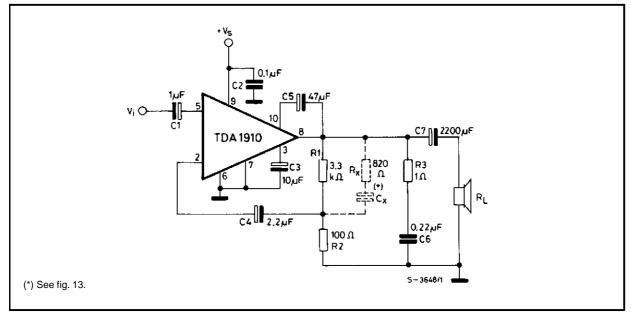


SCHEMATIC DIAGRAM

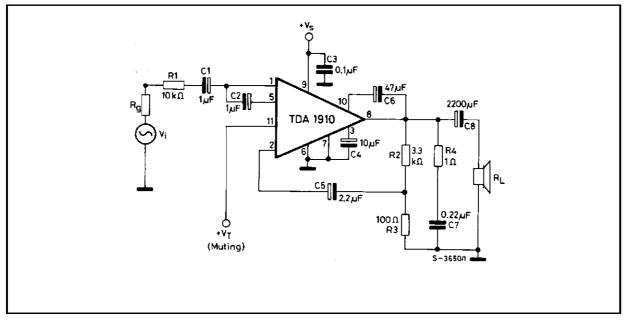




TEST CIRCUIT



MUTING CIRCUIT





THERMAL DATA

Symbol	Parameter		Unit
R _{th j-case}	Thermal resistance junction-case max	3	°C/W

ELECTRICAL CHARACTERISTICS (Refer to the test circuit, $T_{amb} = 25$ °C, R_{th} (heatsink) = 4°C/W, unless otherwise specified)

Symbol	Parameter	Test condition	Min.	Тур.	Max.	Unit
Vs	Supply voltage		8		30	V
Vo	Quiescent output voltage	$V_s = 18V$ $V_s = 24V$	8.3 11.5	9.2 12.4	10 13.4	V
I _d	Quiescent drain current	V _s = 18V V _s = 24V		19 21	32 35	mA
V _{CE sat}	Output stage saturation voltage	I _C = 2A		1		V
		I _C = 3A		1.6		
Po	Output power	$\begin{array}{ll} d = 0.5\% & f = 40 \ to \ 15,000 Hz \\ V_s = 18V & R_L = 4\Omega \\ V_s = 24V & R_L = 4\Omega \\ V_s = 24V & R_L = 8\Omega \end{array}$	6.5 10 7	7 12 7.5		W
			8.5 15 9	9.5 17 10		
d	Harmonic distortion			0.2 0.2 0.2	0.5 0.5 0.5	%
d	Intermodulation distortion			0.2		%
Vi	Input sensitivity	$ \begin{array}{ll} F = 1 \ \text{KHz}, \\ V_s = 18 V \\ v_s = 24 V \\ V_s = 24 V \end{array} \begin{array}{ll} R_L = 4 \Omega & P_o = \ 7 \ \text{W} \\ R_L = 4 \Omega & P_o = 12 \ \text{W} \\ R_L = 8 \Omega & P_o = \ 7.5 \text{W} \end{array} $		170 220 245		mV
Vi	Input saturation voltage (rms)	V _s = 18V V _s = 24V	1.8 2.4			V
Ri	Input resistance (pin 5)	f = 1 KHz	60	100		KΩ
l _d	Drain current	$ \begin{array}{ll} V_{s} = 24V & f = 1 \ KHz \\ R_{L} = 4\Omega & P_{o} = 12W \\ RL = 8\Omega & P_{o} = 7.5W \end{array} $		820 475		mA



Symbol	Parameter	Tes	Test condition			Max.	Unit
h	Efficiency		$ \begin{array}{l} f=1 \ \text{KHz} \\ \Omega & P_{o}=12W \\ \Omega & P_{o}=7.5W \end{array} $		62 65		%
BW	Small signal bandwidth	$V_s = 24V$	$R_L = 4 \Omega \qquad P_o = 1 W$	10	to 120,0	00	Hz
BW	Power bandwidth	$V_s = 24V$ $P_o = 12W$	$\begin{array}{l} R_L = 4\Omega \\ d \leq 5\% \end{array}$	40 to 15,000		Hz	
Gv	Voltage gain (open loop)	f = 1 KHz			75		dB
Gv	Voltage gain (closed loop)	V _s = 24V f = 1 KHz	$R_L = 4\Omega$ Po = 1W	29.5	30	30.5	dB
e _N	Total input noise		$\begin{array}{l} R_{g} = 50\Omega \\ R_{g} = \ 1K\Omega \qquad (^{\circ}) \\ R_{g} = \ 10K\Omega \end{array}$		1.2 1.3 1.5	3.0 3.2 4.0	μV
			$\begin{array}{l} R_{g} = 50\Omega \\ R_{g} = \ 1K\Omega \qquad (^{\circ\circ}) \\ R_{g} = \ 10K\Omega \end{array}$		2.0 2.0 2.2	5.0 5.2 6.0	μV
S/N	Signal to noise ratio	$V_s = 24V$ $P_o = 12W$	$ \begin{array}{l} R_{g} = 10K\Omega \\ R_{g} = 0 \end{array} \qquad (^{\circ}) \end{array} $	97	103 105		dB
		$R_L = 4\Omega$	$ \begin{array}{l} R_{g} = 10K\Omega \\ R_{g} = 0 \end{array} \qquad (^{\circ\circ}) \end{array} $	93	100 100		dB
SVR	Supply voltage rejection	V _s = 24V f _{ripple} = 100 H		50	60		dB
T _{sd}	Thermal sjut-down case (*) temperature		110	125		°C	

ELECTRICAL CHARACTERISTICS (continued)

MUTING FUNCTION (Refer to Muting circuit)

V _T	Muting-off threshold voltage (pin 11)		1.9		4.7	V
VT	Muting-on threshold voltage		0		1.3	V
.,	(pin 11)		6		Vs	
R ₁	Input resistance (pin 1)	Muting off	80	200		KΩ
		Muting on		10	30	Ω
R ₁₁	Input resistance (pin 11)		150			KΩ
A _T	Muting attenuation	$R_g + R_1 = 10 \text{ K}\Omega$	50	60		dB

Note : (°) Weighting filter = curve A. (° °) Filter with noise bandwidth: 22 Hz to 22 KHz. (*) See fig. 29 and fig. 30.



Figure 1. Quiescent output voltage vs. supply voltage

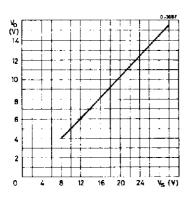


Figure 2. Quiescent drain current vs. supply voltage

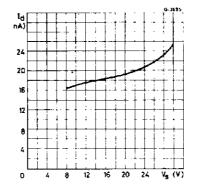


Figure 3. Open loop frequency response

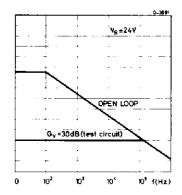


Figure 4. Output power vs. supply voltage

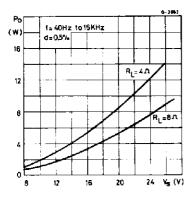


Figure 5. Output power vs. supply voltage

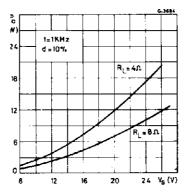


Figure 6. Distortion vs. output power

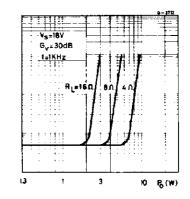


Figure 7. Distortion vs. output power

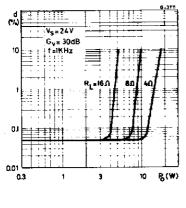


Figure 8. Output power vs. frequency

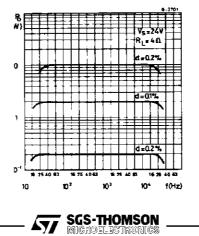
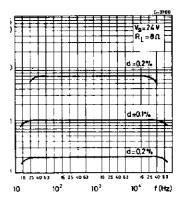


Figure 9. Output power vs. frequency



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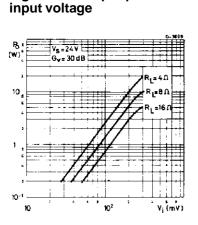


Figure 10. Output power vs.

Figure 11. Output power vs. input voltage

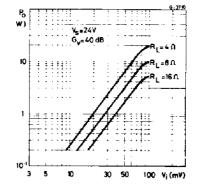


Figure 12. Total input noise vs. source resistance

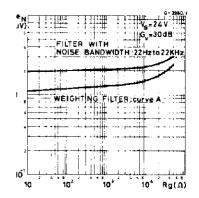


Figure 13. Values of capacitor C_X vs. bandwidth (BW) and gain (G_V)

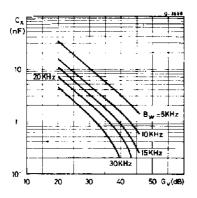


Figure 14. Supply voltage rejection vs. voltage gain

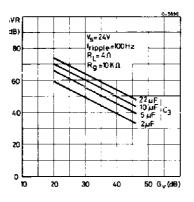


Figure 15. Supply voltage rejection vs. source resistance

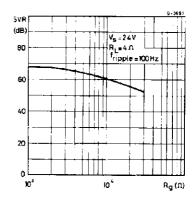


Figure 16. Power dissipation and efficiency vs. output power

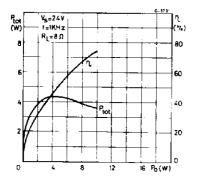


Figure 17. Power dissipation and efficiency vs. output power

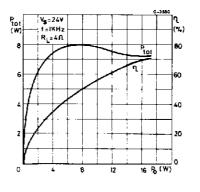
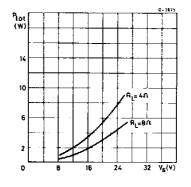
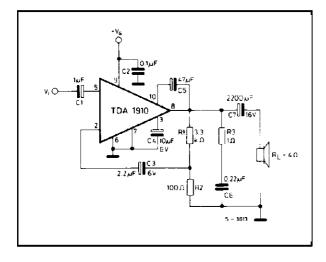


Figure 18. Max power dissipation vs. supply voltage





APPLICATION INFORMATION



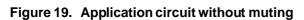


Figure 20. PC board and component lay-out of the circuit of fig. 19 (1:1 scale)

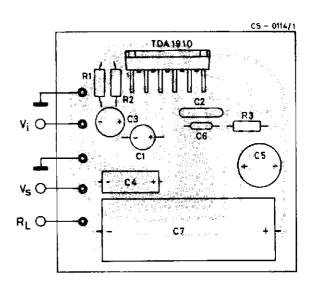
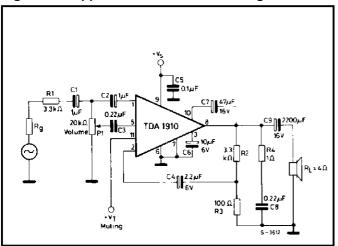


Figure 21. Application circuit with muting

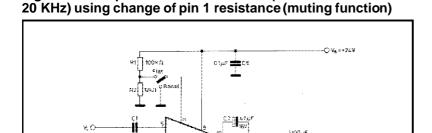


 $\begin{array}{l} \mbox{Performance (circuits of fig. 19 and 21)} \\ \mbox{P}_o = 12W \mbox{ (40 to 15000 Hz, } d \leq 0.5\%) \\ \mbox{V}_s = 24V \\ \mbox{I}_d = 0.82A \\ \mbox{G}_v = 30 \mbox{ dB} \end{array}$



APPLICATION INFORMATION (continued)

0 22



TDA 1910

2200,uF 0.9

+44

116

3 3 | 8 4

100 A

CB1000F

Figure 22. Two position DC tone control (10 dB boost 50 Hz and

Figure 23. Frequency response of the circuit of fig. 22

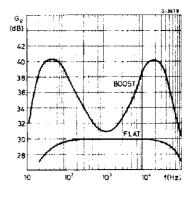
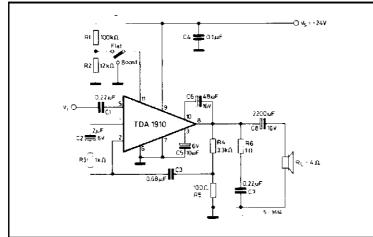


Figure 24. 10 dB 50 Hz boos tone control using change of pin 1 resistance (muting function)





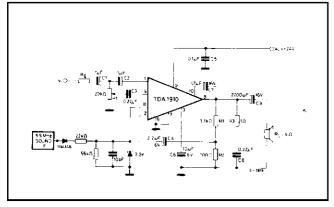


Figure 25. Frequency response of the circuit of fig. 24

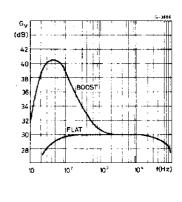
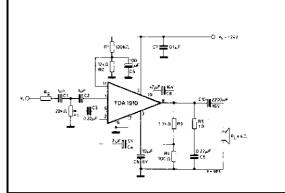


Figure 27. Delayed muting circuit

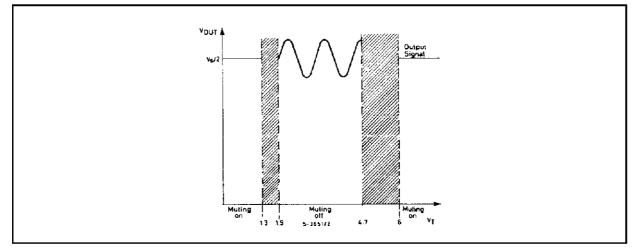




MUTING FUNCTION

The output signal can be inhibited applying a DC voltage V_T to pin 11, as shown in fig. 28

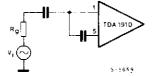
Figure 28



The input resistance at pin 1 depends on the threshold voltage VT at pin 11 and is typically.

$R_1 = 200 \text{ K}\Omega$	@	$1.9V \le V_T \le 4.7V$	muting-off
R1 = 10 Ω	@	$\begin{array}{l} 0V \leq V_T \leq 1.3V \\ 6V \leq V_T \leq V_s \end{array}$	muting-on

Referring to the following input stage, the possible attenuation of the input signal and therefore of the output signal can be found using the following expression.



 $A_T = \frac{V_i}{V_5} = \frac{R_g + R_5 //R_1}{R_5 //R_1}$

where R5 $\cong 100 \text{ K}\Omega$

Considering Rg = 10 K Ω the attenuation in the muting-on condition is typically A_T = 60 dB. In the muting-off condition, the attenuation is very low, typically 1.2 dB.

A very low current is necessary to drive the threshold voltage V_T because the input resistance at pin 11 is greater than 150 K Ω . The muting function can be used in many cases, when a temporary inhibition of the output signal is requested, for example:

- in switch-on condition, to avoid preamplifier power-on transients (see fig. 27)

- during commutations at the input stages.

- during the receiver tuning.

The variable impedance capability at pin 1 can be useful in many applications and we have shown 2 examples in fig. 22 and 24, where it has been used to change the feedback network, obtaining 2 different frequency responses.



APPLICATION SUGGESTION

The recommended values of the components are those shown on application circuit of fig. 21. Different values can be used.

The following table can help the designer.

Component	Raccom.	Purpose	Larger than	Smaller than	Allowed range	
	value		recommended value	recommended value	Min.	Max.
R _g + R ₁	10KΩ	Input signal imped. for muting operation	Increase of the atte- nuation in muting-on condition. Decrease of the input sensitivity.	Decrease of the attenuation in muting on condition.		
R_2	3.3ΚΩ	Close loop gain setting.	Increase of gain.	Decrease of gain. Increase quiescent current.	9 R ₃	
R ₃	100Ω	Close loop gain setting.	Decrease of gain.	Increase of gain.		R ₂ /9
R4	1Ω	Frequency stability	Danger of oscillation at high frequencies with inductive loads.			
P ₁	20ΚΩ	Volume potentiometer.	Increase of the switch-on noise.	Decrease of the input impedance and of the input level.	10KΩ	100KΩ
$\begin{array}{c} C_1\\ C_2\\ C_3 \end{array}$	1 μF 1 μF 0.22μF	Input DC decoupling.		Higher low frequency cutoff.		
C ₄	2.2μF	Inverting input DC decoupling.	Increase of the switch-on noise.	Higher low frequency cutoff.	0.1µF	
C ₅	0.1µF	Supply voltage bypass.		Danger of oscillations.		
C ₆	10μF	Ripple rejection.	Increase of SVR. Increase of the switch-on time	Degradation of SVR	2.2μF	100µF
C ₇	47μF	Bootstrap.		Increase of the distor- tion at low frequency.	10µF	100µF
C ₈	0.22µF	Frequency stability.		Danger of oscillation.		
C ₉	$\begin{array}{c} 2200 \mu F \\ (R_L = 4 \Omega) \\ 1000 \ \mu F \\ (R_L = 8 \Omega) \end{array}$	Output DC decoupling.		Higher low frequency cutoff.		



THERMAL SHUT-DOWN

The presence of a thermal limiting circuit offers the following advantages:

- An overload on the output (even if it is permanent), or an above limit ambient temperature can be easily supported since the T_j cannot be higher than 150°C.
- 2) The heatskink can have a smaller factor of safety compared with that of a conventional

circuit. There is no possibility of device damage due to high junction temperature.

If for any reason, the junction temperature increases up to 150°C, the thermal shut-down simply reduces the power dissipation and the current consumption.

The maximum allowable power dissipation depends upon the size of the external heatsink (i.e. its thermal resistance); fig. 31 shows this dissipable power as a function of ambient temperature for different thermal resistance.

Figure 29. Output power and drain current vs. case temperature

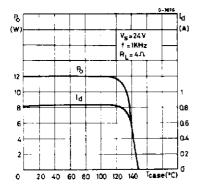


Figure 30. Output power and drain current vs. case temperature

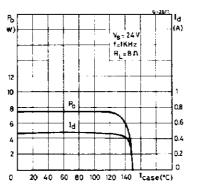
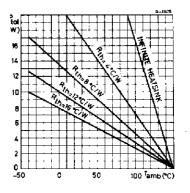


Figure 31. Maximum allow able power dissipation vs. ambient temperature



MOUNTING INSTRUCTIONS

The power dissipated in the circuit must be removed by adding an external heatsink.

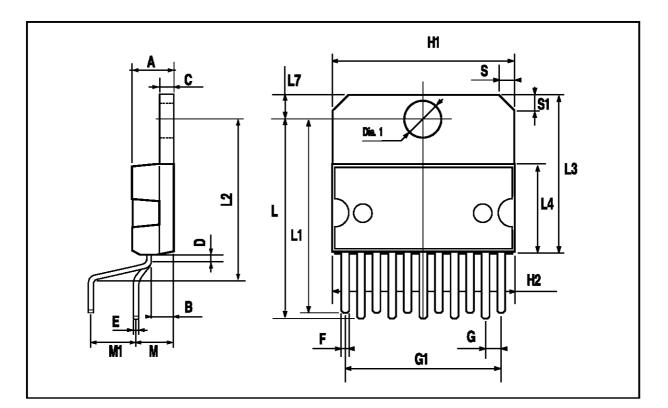
Thanks to the Multiwatt® package attaching the heatsink is very simple, a screw or a compression

spring (clip) being sufficient. Between the heatsink and the package it is better to insert a layer of silicon grease, to optimize the thermal contact; no electrical isolation is needed between the two surfaces.



DIM.	mm			inch			
DIM.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
A			5			0.197	
В			2.65			0.104	
С			1.6			0.063	
D		1			0.039		
E	0.49		0.55	0.019		0.022	
F	0.88		0.95	0.035		0.037	
G	1.57	1.7	1.83	0.062	0.067	0.072	
G1	16.87	17	17.13	0.664	0.669	0.674	
H1	19.6			0.772			
H2			20.2			0.795	
L	21.5		22.3	0.846		0.878	
L1	21.4		22.2	0.843		0.874	
L2	17.4		18.1	0.685		0.713	
L3	17.25	17.5	17.75	0.679	0.689	0.699	
L4	10.3	10.7	10.9	0.406	0.421	0.429	
L7	2.65		2.9	0.104		0.114	
М	4.1	4.3	4.5	0.161	0.169	0.177	
M1	4.88	5.08	5.3	0.192	0.200	0.209	
S	1.9		2.6	0.075		0.102	
S1	1.9		2.6	0.075		0.102	
Dia1	3.65		3.85	0.144		0.152	

MULTIWATT 11 VERTICAL PACKAGE MECHANICAL DATA





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